





CD54HC251, CD74HC251, CD54HCT251, CD74HCT251 SCHS169D – NOVEMBER 1998 – REVISED MARCH 2022

CDx4HC251, CDx4HCT251 High-Speed CMOS Logic 8-Input Multiplexer, Three-State

1 Features

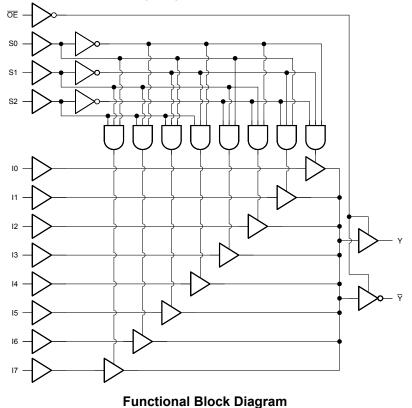
- · Selects one of eight binary data inputs
- Three-state output capability
- True and complement outputs
- Typical (data to output) propagation delay of 14 ns at V_{CC} = 5 V, C_L = 15 pF, T_A = 25 °C
- Fanout (over temperature range)
 - Standard outputs : 10 LSTTL loads
 Bus driver outputs : 15 LSTTL loads
- Wide operating temperature range : 55 °C to 125 °C
- · Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips
- HC types
 - 2 V to 6 V operation
 - High noise immunity : N_{IL} = 30 %, N_{IH} = 30% of V_{CC} at V_{CC} = 5 V
- HCT types
 - 4.5 V to 5.5 V operation
 - Direct LSTTL input logic compatibility, V_{IL} = 0.8
 V (Max), V_{IH} = 2 V (Min)
 - CMOS input compatibility, $I_I \le 1 \mu A$ at V_{OL} , V_{OH}

2 Description

The 'HC251 and 'HCT251 are 8-channel digital multiplexers with three-state outputs, fabricated with high-speed silicongate CMOS technology. Together with the low power consumption of standard CMOS integrated circuits, they possess the ability to drive 10 LSTTL loads. The three-state feature makes them ideally suited for interfacing with bus lines in a bus-oriented system.

Device Information											
PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM)									
CD54HC251F	CDIP (16)	24.38 mm × 6.92 mm									
CD54HCT251F	CDIP (16)	24.38 mm × 6.92 mm									
CD74HC251M	SOIC (16)	9.90 mm × 3.90 mm									
CD74HCT251M	SOIC (16)	9.90 mm × 3.90 mm									
CD74HC251E	PDIP (16)	19.31 mm × 6.35 mm									
CD74HCT251E	PDIP (16)	19.31 mm × 6.35 mm									

(1) For all available packages, see the orderable addendum at the end of the data sheet.



An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.



Table of Contents

4 Pin Configuration and Functions35 Specifications45.1 Absolute Maximum Ratings45.2 Recommended Operating Conditions ⁽¹⁾ 45.3 Thermal Information45.4 Electrical Characteristics55.5 Switching Characteristics66 Parameter Measurement Information77 Detailed Description9	2	Features. Description. Revision History	1
5 Specifications45.1 Absolute Maximum Ratings45.2 Recommended Operating Conditions ⁽¹⁾ 45.3 Thermal Information45.4 Electrical Characteristics55.5 Switching Characteristics66 Parameter Measurement Information77 Detailed Description9			
5.2 Recommended Operating Conditions ⁽¹⁾ 45.3 Thermal Information45.4 Electrical Characteristics55.5 Switching Characteristics66 Parameter Measurement Information77 Detailed Description9			
5.3 Thermal Information45.4 Electrical Characteristics55.5 Switching Characteristics66 Parameter Measurement Information77 Detailed Description9			
5.4 Electrical Characteristics55.5 Switching Characteristics66 Parameter Measurement Information77 Detailed Description9		5.2 Recommended Operating Conditions ⁽¹⁾	4
5.5 Switching Characteristics66 Parameter Measurement Information77 Detailed Description9		5.3 Thermal Information	4
6 Parameter Measurement Information		5.4 Electrical Characteristics	5
7 Detailed Description		5.5 Switching Characteristics	6
	6	Parameter Measurement Information	7
	7	Detailed Description	9
		7.1 Overview	
7.2 Functional Block Diagram9		7.2 Functional Block Diagram	9

7.3 Device Functional Modes	10
8 Power Supply Recommendations	11
9 Layout	11
9.1 Layout Guidelines	11
10 Device and Documentation Support	12
10.1 Documentation Support	12
10.2 Receiving Notification of Documentation Upda	tes12
10.3 Support Resources	12
10.4 Trademarks	12
10.5 Electrostatic Discharge Caution	12
10.6 Glossary	
11 Mechanical, Packaging, and Orderable	
Information	12

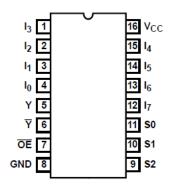
3 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	hanges from Revision C (October 2003) to Revision D (March 2022)	Page
•	Updated the numbering, formatting, tables, figures, and cross-references throughout the doucment to re	flect
	modern data sheet standards	1



4 Pin Configuration and Functions



J, N, or D Package 16-Pin CDIP, PDIP, or SOIC Top View



5 Specifications

5.1 Absolute Maximum Ratings

			MIN	MAX	UNIT
V _{CC}	Supply voltage range		-0.5	7	V
I _{IK}	Input diode current ⁽²⁾	$V_{\rm I} < 0.5 \ V \ {\rm or} \ V_{\rm I} > V_{\rm CC} + 0.5 \ V$		±20	mA
I _{ок}	Output diode current ⁽²⁾	$V_{\rm O}$ < - 0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V		±20	mA
lo	Drain current, per output	$-0.5 V < V_O < V_{CC} + 0.5 V$		±25	mA
Io	Output source or sing current per output pin	$V_{\rm O}$ > – 0.5 V or $V_{\rm O}$ < $V_{\rm CC}$ + 0.5 V		±25	mA
	Continuous current through V _{CC} c	or GND		±50	mA
TJ	Junction temperature			150	°C
T _{stg}	Storage temperature	Storage temperature			
	Lead temperature (Soldering 10s)) (SOIC - lead tips only)		300	°C

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

5.2 Recommended Operating Conditions⁽¹⁾

			MIN	MAX	UNIT
V	Supply voltage range	HC Types	2	6	V
V _{CC}		HCT Types	4.5	5.5	V
V _I , V _O	DC input or output voltage		0	V _{CC}	V
		2 V		1000	
t _t	Input rise and fall time	4.5 V		500	ns
		6 V		400	
T _A	Temperature range		- 55	125	C°

 All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report Implications of Slow or Floating SMOS Inputs, literature number SCBA004.

5.3 Thermal Information

		D (SOIC)	N (PDIP)	
THERMAL METRI	c	16 PINS	16 PINS	UNIT
R _{θJA}	Junction-to-ambient thermal resistance ⁽¹⁾	67	73	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC package thermal metrics application report.



5.4 Electrical Characteristics

PARAMETER		TEST	Vcc	25°C			–40°C t	o 85°C	–55°C to 125°C		UNIT	
	PARAMETER	CONDITIONS ⁽¹⁾	(V)	MIN TYP I		MAX	MIN	MIN MAX		MAX	UNIT	
HC TYPES	6											
			2	1.5			1.5		1.5		V	
V _{IH}	High-level input voltage		4.5	3.15			3.15		3.15		V	
			6	4.2			4.2		4.2		V	
			2			0.5		0.5		0.5	V	
V _{IL}	Low-level input voltage		4.5			1.35		1.35		1.35	V	
			6			1.8		1.8		1.8	V	
		I _{OH} = – 20μA	2	1.9			1.9		1.9		V	
	High-level output voltage CMOS loads	Ι _{ΟΗ} = – 20μΑ	4.5	4.4			4.4		4.4		V	
V _{OH}		I _{OH} = – 20µА	6	5.9			5.9		5.9		V	
	High-level output voltage	I _{OH} = – 6mA	4.5	3.98			3.84		3.7		V	
	TTL loads	I _{OH} = – 7.8mA	6	5.48			5.34		5.2		V	
		Ι _{ΟL} = 20μΑ	2			0.1		0.1		0.1	V	
	Low-level output voltage CMOS loads	I _{OL} = 20μA	4.5			0.1		0.1		0.1	V	
V _{OL}		I _{OL} = 20μΑ	6			0.1		0.1		0.1	V	
	Low-level output voltage	I _{OL} = 6mA	4.5			0.26		0.33		0.4	V	
	TTL loads	I _{OL} = 7.8mA	6			0.26		0.33		0.4	V	
I	Input leakage current	V _{CC} or GND	6			±0.1		±1		±1	μA	
сс	Supply current	V _{CC} or GND	6			8		80		160	μA	
oz	Three-state leakage current		6			±0.5		±0.5		±10	μA	
НСТ ТҮРЕ	S	1	1							1		
V _{IH}	High-level input voltage		4.5 to 5.5	2			2		2		V	
V _{IL}	Low-level input voltage		4.5 to 5.5			0.8		0.8		0.8	V	
	High-level output voltage CMOS loads	Ι _{ΟΗ} = – 20μΑ	4.5	4.4			4.4		4.4		V	
V _{OH}	High-level output voltage TTL loads	I _{OH} = – 6mA	4.5	3.98			3.84		3.7		V	
,	Low-level output voltage CMOS loads	I _{OL} = 20μΑ	4.5			0.1		0.1		0.1	V	
V _{OL}	Low-level output voltage TTL loads	I _{OL} = 6mA	4.5			0.26		0.33		0.4	V	
1	Input leakage current	V _{CC} and GND	5.5			±0.1		±1		±1	μA	
сс	Supply Current	V _{CC} and GND	5.5			8		80		160	μA	
oz	Three-state leakage current		6			±0.5		±5.0		±10	μA	
		S0, S1, S2	4.5 to 5.5		55	198		247.5		269.5	μA	
∆I _{CC} ⁽²⁾ (3)	Additional supply current per input pin	10 - 17	4.5 to 5.5		50	180		225		245	μA	
		ŌĒ	4.5 to 5.5		265	954		1192.5		1298.5	μA	

V_I = V_{IH} or V_{IL}, unless otherwise noted.
 For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA..

(3) Inputs held at $V_{CC} - 2.1$.

Copyright © 2022 Texas Instruments Incorporated



5.5 Switching Characteristics

Input t_t = 6ns. Unless otherwise specified, C_L = 50pF

	PARAMETER	V _{cc} (V)	25°C		-40°C to 85°C	-55°C to 125°C	UNIT		
			ТҮР	MAX	MAX	MAX			
HC TYPES									
		2		245	305	370			
t _{pd}	Select to outputs	4.5	21 ⁽¹⁾	49	61	74	ns		
	-	6		42	52	63			
		2		175	220	265			
t _{pd}	Data to outputs	4.5	12 ⁽¹⁾	35	44	53	ns		
	-	6		30	37	45			
		2		140	175	210			
t _{pd} E	Enable to high Z and enable from high Z	4.5	11 ⁽¹⁾	28	35	42	ns		
	-	6		24	30	36			
		2		75	95	110			
t _t	Output transition times	4.5		15	19	22	ns		
	-	6		13	16	19			
C _i	Input capacitance			10	10	10	pF		
Co	Three-state output capacitance			15	15	15	pF		
C _{pd} ⁽³⁾ ⁽⁴⁾	Power dissipation capacitance	5	60 ⁽²⁾				pF		
HCT TYPES	3			I	L	I			
t _{pd}	Select to outputs	4.5	18 ⁽¹⁾	42	53	63	ns		
t _{pd}	Data to outputs	4.5	12 ⁽¹⁾	35	44	53	ns		
t _{pd}	Enable to high Z and enable from high Z	4.5	12 ⁽¹⁾	30	38	45	ns		
t _t	Output transition times	4.5		15	19	22	ns		
Ci	Input capacitance			10	10	10	pF		
C _{pd} ^{(3) (4)}	Power dissipation capacitance	5	60 ⁽²⁾				pF		

(1) Typical value tested at 5V, C_L = 15pF.

(1) Typical value tosted at 5V, (2) Typical value tested at 5V. (3) C_{PD} is used to determine the dynamic power consumption, per channel. (4) $P_D = V_{CC} {}^2f_i(C_{PD} + C_L)$ where f_i = input frequency, C_L = output load capacitance, V_{CC} = supply voltage.

Copyright © 2022 Texas Instruments Incorporated

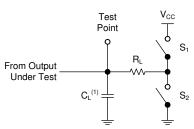


6 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, Z_O = 50 Ω , t_t < 6 ns.

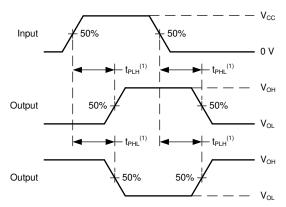
For clock inputs, f_{max} is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.

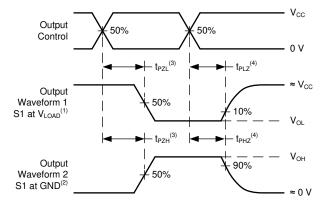


(1) C_L includes probe and test-fixture capacitance.





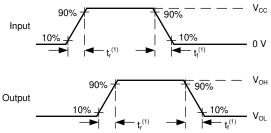




⁽¹⁾ t_{PLZ} and t_{PHZ} are the same as $t_{\text{dis}}.$

(2) t_{PZL} and t_{PZH} are the same as t_{en} .

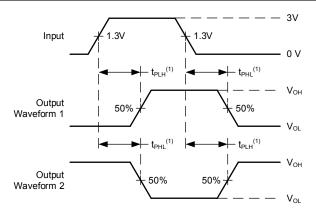
Figure 6-3. Voltage Waveforms, Standard CMOS Inputs Propagation Delays



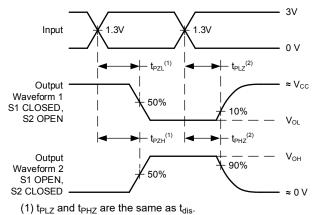
(1) The greater between t_r and t_f is the same as t_t .

Figure 6-4. Voltage Waveforms, Input and Output Transition Times for Standard CMOS Inputs

CD54HC251, CD74HC251, CD54HCT251, CD74HCT251 SCHS169D – NOVEMBER 1998 – REVISED MARCH 2022



 (1) The greater between t_{PLH} and t_{PHL} is the same as t_{pd}.
 Figure 6-5. Voltage Waveforms, Propagation Delays for TTL-Compatible Inputs



Texas

INSTRUMENTS

www.ti.com

(2) t_{PZL} and t_{PZH} are the same as t_{en} .

Figure 6-6. Voltage Waveforms, TTL-Compatible CMOS Inputs Propagation Delays



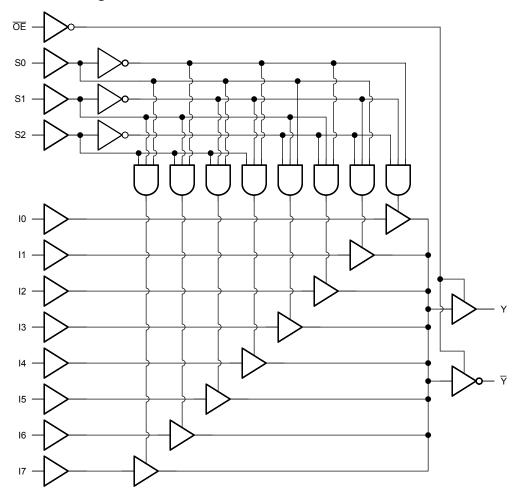
7 Detailed Description

7.1 Overview

The 'HC251 and 'HCT251 are 8-channel digital multiplexers with three-state outputs, fabricated with high-speed silicongate CMOS technology. Together with the low power consumption of standard CMOS integrated circuits, they possess the ability to drive 10 LSTTL loads. The three-state feature makes them ideally suited for interfacing with bus lines in a bus-oriented system.

This multiplexer features both true (Y) and complement (\overline{Y}) outputs as well as an output enable (\overline{OE}) input. The \overline{OE} must be at a low logic level to enable this device. When the \overline{OE} input is high, both outputs are in the high-impedance state. When enabled, address information on the data select inputs determines which data input is routed to the Y and \overline{Y} outputs. The 'HCT251 logic family is speed, function, and pin-compatible with the standard 'LS251.

7.2 Functional Block Diagram





7.3 Device Functional Modes

Table 7-1. Truth Table⁽¹⁾

		INPUTS		OUT	PUT
	SELECT				
S2	S1	S0	OUTPUT CONTROL OE	Y	Ŧ
Х	Х	Х	Н	Z	Z
L	L	L	L	I ₀	Ī ₀
L	L	Н	L	I ₁	Ī ₁
L	Н	L	L	l ₂	Ī2
L	Н	Н	L	l ₃	Ī3
Н	L	L	L	I ₄	Ī4
Н	L	Н	L	I ₅	Ī 5
Н	Н	L	L	I ₆	Ī ₆
Н	Н	Н	L	I ₇	Ī ₇

(1) H = High voltage level.

L = Low voltage level.

X = Dont care.

Z = High impedance (Off). $I_0, I_1... I_7$ = The level of the respective input.



8 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1-µF capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1-µF and 1-µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

9 Layout

9.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.



10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

10.1 Documentation Support

10.1.1 Related Documentation

10.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

10.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

10.4 Trademarks

TI E2E[™] is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

10.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10.6 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
5962-9052401MEA	ACTIVE	CDIP	J	16	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9052401ME A CD54HCT251F3A	Samples
CD54HC251F	ACTIVE	CDIP	J	16	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	CD54HC251F	Samples
CD54HC251F3A	ACTIVE	CDIP	J	16	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	8512501EA CD54HC251F3A	Samples
CD54HCT251F3A	ACTIVE	CDIP	J	16	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9052401ME A CD54HCT251F3A	Samples
CD74HC251E	ACTIVE	PDIP	Ν	16	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC251E	Samples
CD74HC251M	ACTIVE	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC251M	Samples
CD74HC251M96	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC251M	Samples
CD74HC251MT	ACTIVE	SOIC	D	16	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC251M	Samples
CD74HCT251E	ACTIVE	PDIP	N	16	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HCT251E	Samples
CD74HCT251M	ACTIVE	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT251M	Samples
CD74HCT251M96	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT251M	Samples
CD74HCT251MT	ACTIVE	SOIC	D	16	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT251M	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.



www.ti.com

PACKAGE OPTION ADDENDUM

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF CD54HC251, CD54HCT251, CD74HC251, CD74HCT251 :

- Catalog : CD74HC251, CD74HCT251
- Military : CD54HC251, CD54HCT251

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Military QML certified for Military and Defense Applications



Texas

STRUMENTS

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD74HC251M96	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
CD74HCT251M96	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1



www.ti.com

PACKAGE MATERIALS INFORMATION

9-Aug-2022



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CD74HC251M96	SOIC	D	16	2500	340.5	336.1	32.0
CD74HCT251M96	SOIC	D	16	2500	340.5	336.1	32.0

TEXAS INSTRUMENTS

www.ti.com

9-Aug-2022

TUBE



- B - Alignment groove width

*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
CD74HC251E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HC251E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HC251M	D	SOIC	16	40	507	8	3940	4.32
CD74HCT251E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT251E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT251M	D	SOIC	16	40	507	8	3940	4.32

D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.



4211283-4/E 08/12

D (R-PDSO-G16) PLASTIC SMALL OUTLINE Stencil Openings (Note D) Example Board Layout (Note C) –16x0,55 -14x1,27 -14x1,27 16x1,50 5,40 5.40 Example Non Soldermask Defined Pad Example Pad Geometry (See Note C) 0,60 .55 Example 1. Solder Mask Opening (See Note E) -0,07 All Around

NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



J (R-GDIP-T**) 14 LEADS SHOWN

CERAMIC DUAL IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- \triangle The 20 pin end lead shoulder width is a vendor option, either half or full width.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2022, Texas Instruments Incorporated